

Applicant : Shunpei azaki, et al.
Serial No. : 10/033,100
Filed : October 25, 2001
Page : 2 of 5

Attorney's Docket No.: 07977-
287001 / US5276

In the claims:

Please amend claims 23 and 24, add claims 28-33 as follows.

Claims 1-8 (Withdrawn).

9. (Original) A film formation method comprising the steps of:

setting different temperatures to a material plural times in an evaporation source comprising the material to purify the material by sublimation stepwise; and

forming a thin film on a substrate using the purified material.

10. (Original) A film formation method according to claim 9, wherein the material is an EL material.

Claims 11-21 (Withdrawn).

22. (Original) A film formation method comprising the steps of:

evaporating a material in a first system controlled to a first temperature;

controlling a second system to a second temperature to change the material into a first gas and a first solid;

removing the first gas;

evaporating the first solid in the second system controlled to the first temperature;

controlling a third system to a third temperature to change the evaporated first solid into a second gas and a second solid; and

Applicant : Shunpei Mazaki, et al.
Serial No. : 10/033,100
Filed : October 25, 2001
Page : 3 of 5

Attorney Docket No.: 07977-
287001 / US5276

forming a thin film using the second gas over a substrate.

23. (Currently Amended) A film formation method comprising the steps of:

evaporating a material in a first system controlled to a first temperature;

controlling a second system to a second temperature to change the material into a ~~first~~ gas and a ~~first~~ solid;

removing the ~~first~~ gas; and

evaporating the ~~first~~ solid in the second system controlled to the first temperature.

24. (Currently Amended) A film formation method comprising the steps of:

evaporating a material in a first system controlled to a first temperature;

controlling a second system to a second temperature to change the material into a ~~first~~ gas and a ~~first~~ solid; and

forming a thin film using the ~~second~~ gas over a substrate.

25. (Original) A film formation method according to claim 22, wherein the material is an EL material.

26. (Original) A film formation method according to claim 23, wherein the material is an EL material.

27. (Original) A film formation method according to claim 24, wherein the material is an EL material.

Applicant : Shunpei Mazaki, et al.
Serial No. : 10/033,100
Filed : October 25, 2001
Page : 4 of 5

Attorney Docket No.: 07977-
287001 / US5276

28. (New) A film formation method comprising the steps of:
evaporating a solid including an EL material to form a
gas including the EL material;
moving the gas including the EL material with a
carrier gas, and a temperature of the gas including the EL
material gradually decrease in accordance with the moving;
precipitating the EL material in one position to form
a precipitated EL material; and
forming a thin film using the precipitated EL
material.

29. (New) A film formation method according to claim 28,
wherein the carrier gas is one of nitrogen and a noble gas.

30. (New) A film formation method according to claim 28,
wherein the moving step is conducted in a reduced pressure
state.

31. (New) A film formation method comprising the steps of:
evaporating a solid including an EL material to form a
gas including the EL material in a first chamber;
moving the gas including the EL material with a
carrier gas in a second chamber, and a temperature of the gas
including the EL material gradually decrease in accordance with
the moving;
precipitating the EL material in one position to form
a precipitated EL material in the second chamber; and
forming a thin film using the precipitated EL material
in a third chamber.

Applicant : Shunpei [REDACTED] azaki, et al.
Serial No. : 10/033,100
Filed : October 25, 2001
Page : 5 of 5

Attorney [REDACTED] Docket No.: 07977-
287001 / US5276

32. (New) A film formation method according to claim 31,
wherein the carrier gas is one of nitrogen and a noble gas.

*Pl
cont.* 33. (New) A film formation method according to claim 31,
wherein the moving step is conducted in a reduced pressure
state.
